NSN 5962-01-352-7910

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View Online at https://aerobasegroup.com/nsn/5962-01-352-7910

Overall Length:

0.540 inches

Overall Height:

Between 0.045 inches and 0.100 inches

Overall Width:

Between 0.745 inches and 1.040 inches

Body Length:

0.540 inches

Body Width:

Between 0.245 inches and 0.300 inches

Body Height:

Between 0.045 inches and 0.100 inches

Maximum Power Dissipation Rating:

1.1 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Electrostatic sensitive and monolithic and high impedance and w/clock and w/disable

Inclosure Material:

Ceramic

Inclosure Configuration:

Flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

14 input

Case Outline Source And Designator:

F-9 mil-m-38510

Current Rating Per Characteristic:

190.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

Registered and-or gate array

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

20.00 nanoseconds propagation delay time, high to low level output and 20.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Pal

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Special Features:

Nuclear hardness critical items

Nuclear Hardness Critical Feature:

Hardened

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 flat leads

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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